

# 2SC5346

## Silicon NPN epitaxial planer type

For low-frequency high breakdown voltage amplification  
Complementary to 2SA1982

### Features

- Satisfactory linearity of forward current transfer ratio  $h_{FE}$ .
- High collector to emitter voltage  $V_{CEO}$ .
- Small collector output capacitance  $C_{ob}$ .

### Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	150	V
Collector to emitter voltage	$V_{CEO}$	150	V
Emitter to base voltage	$V_{EBO}$	5	V
Peak collector current	$I_{CP}$	100	mA
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C^{*1}$	1.0	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

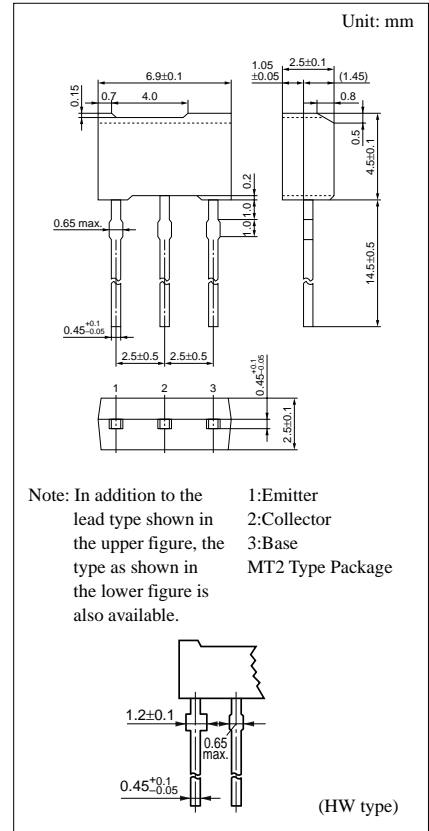
\*1 Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

### Electrical Characteristics (Ta=25°C)

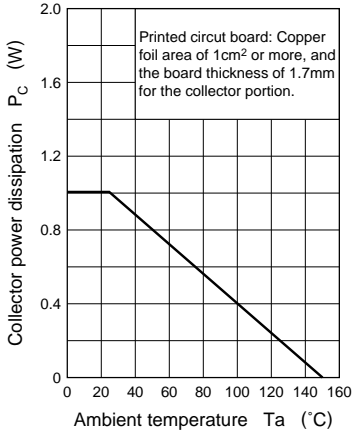
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 100V, I_E = 0$			1	μA
Collector to emitter voltage	$V_{CEO}$	$I_C = 0.1mA, I_B = 0$	150			V
Emitter to base voltage	$V_{EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	$h_{FE}^{*1}$	$V_{CE} = 5V, I_C = 10mA$	130		330	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30mA, I_B = 3mA$			1	V
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$		150	300	mV
Transition frequency	$f_T$	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		160		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$			5	pF

\*1  $h_{FE}$  Rank classification

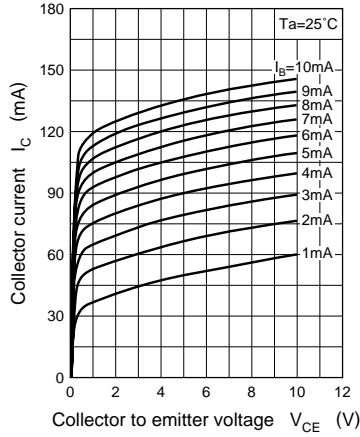
Rank	R	S
$h_{FE}$	130 ~ 220	185 ~ 330



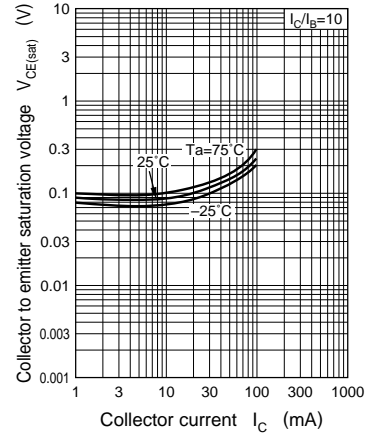
$P_C - T_a$



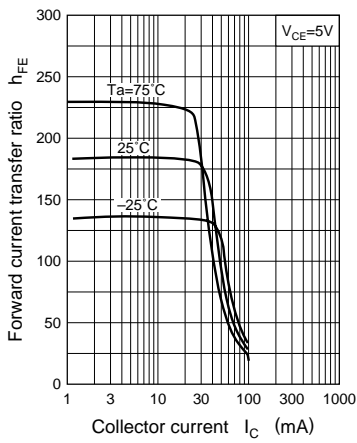
$I_C - V_{CE}$



$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$C_{ob} - V_{CB}$

